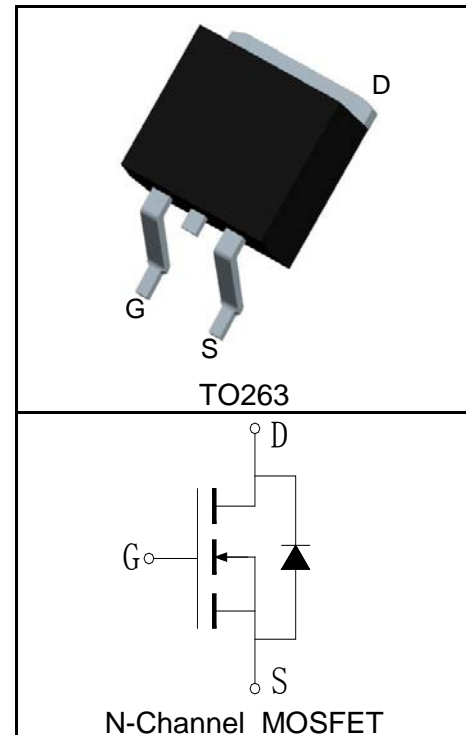


Features

- 150V/80A,
 $R_{DS(ON)} = 31m\Omega(Typ.)@V_{GS}=10V$
- Avalanche Rated
- Reliable and Rugged
- Lead Free and Green Devices Available

Applications

- Automotive applications and a wide variety of other applications
- High Efficiency Synchronous in SMPS
- High Speed Power Switching

Pin Description

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_C=25^\circ C$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	150	V
V_{GSS}	Gate-Source Voltage	± 25	
T_J	Maximum Junction Temperature	175	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
I_S	Diode Continuous Forward Current	$T_C=25^\circ C$ 80	A
Mounted on Large Heat Sink			
$I_{DP}^{①}$	300 μs Pulse Drain Current Tested	$T_C=25^\circ C$ 300	A
$I_D^{②}$	Continuous Drain Current($V_{GS}=10V$)	$T_C=25^\circ C$ 80	A
		$T_C=100^\circ C$ 60	
P_D	Maximum Power Dissipation	$T_C=25^\circ C$ 176	W
		$T_C=100^\circ C$ 88	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	0.85	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	$^\circ C/W$
Drain-Source Avalanche Ratings			
$E_{AS}^{③}$	Avalanche Energy, Single Pulsed	169	mJ

Electrical Characteristics ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)

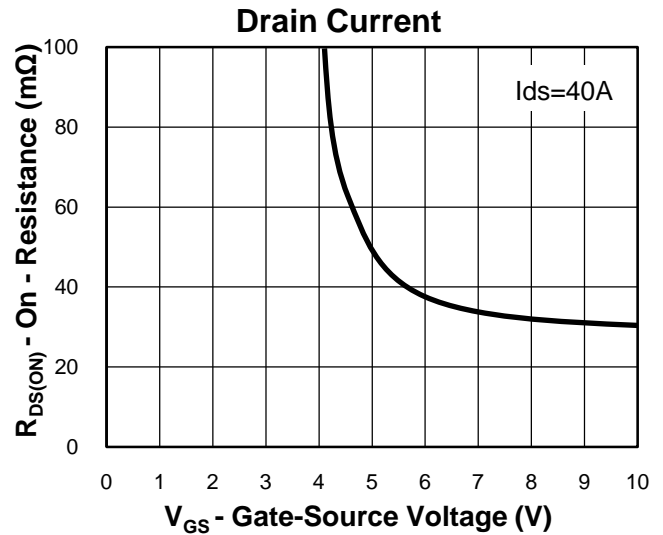
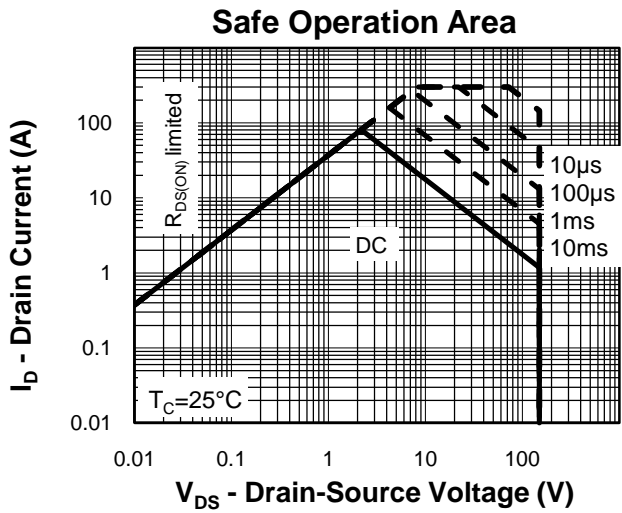
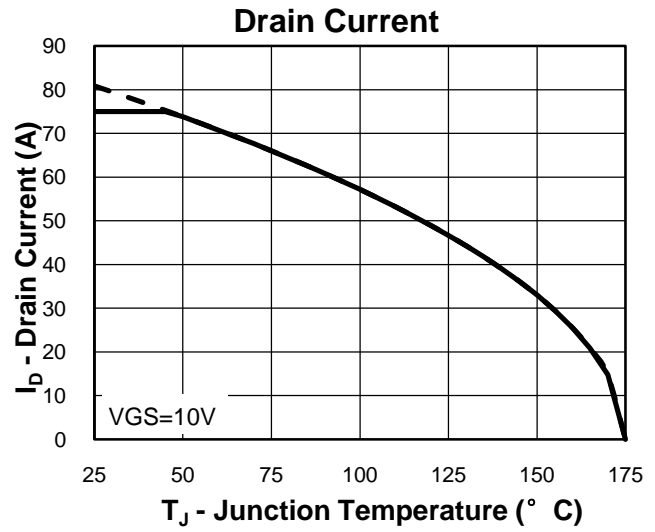
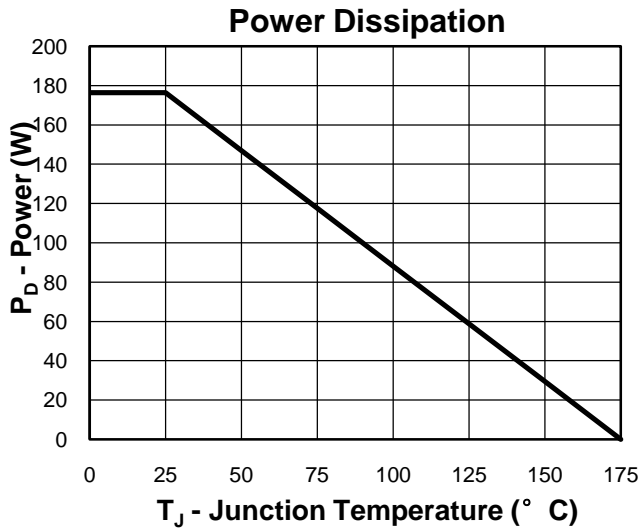
Symbol	Parameter	Test Condition	RU80N15S			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	150			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=150V, V_{GS}=0V$			1	μA
		$T_J=125^\circ\text{C}$			30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2	3	4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(4)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=40A$		31	36	m Ω
Diode Characteristics						
$V_{SD}^{(4)}$	Diode Forward Voltage	$I_{SD}=40A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=40A, di_{SD}/dt=100A/\mu s$		68		ns
Q_{rr}	Reverse Recovery Charge			130		nC
Dynamic Characteristics⁽⁵⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		1		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=30V,$ Frequency=1.0MHz		3800		pF
C_{oss}	Output Capacitance			550		
C_{riss}	Reverse Transfer Capacitance			250		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=35V, R_L=35\Omega,$ $I_{DS}=1A, V_{GEN}=10V,$ $R_G=10\Omega$		18		ns
t_r	Turn-on Rise Time			32		
$t_{d(OFF)}$	Turn-off Delay Time			80		
t_f	Turn-off Fall Time			56		
Gate Charge Characteristics⁽⁵⁾						
Q_g	Total Gate Charge	$V_{DS}=30V, V_{GS}=10V,$ $I_{DS}=40A$		90		nC
Q_{gs}	Gate-Source Charge			25		
Q_{gd}	Gate-Drain Charge			30		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 75A.
 - ③ Limited by T_{Jmax} , $I_{AS}=26A$, $V_{DD}=48V$, $R_G=50\Omega$, Starting $T_J=25^\circ\text{C}$.
 - ④ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑤ Guaranteed by design, not subject to production testing.

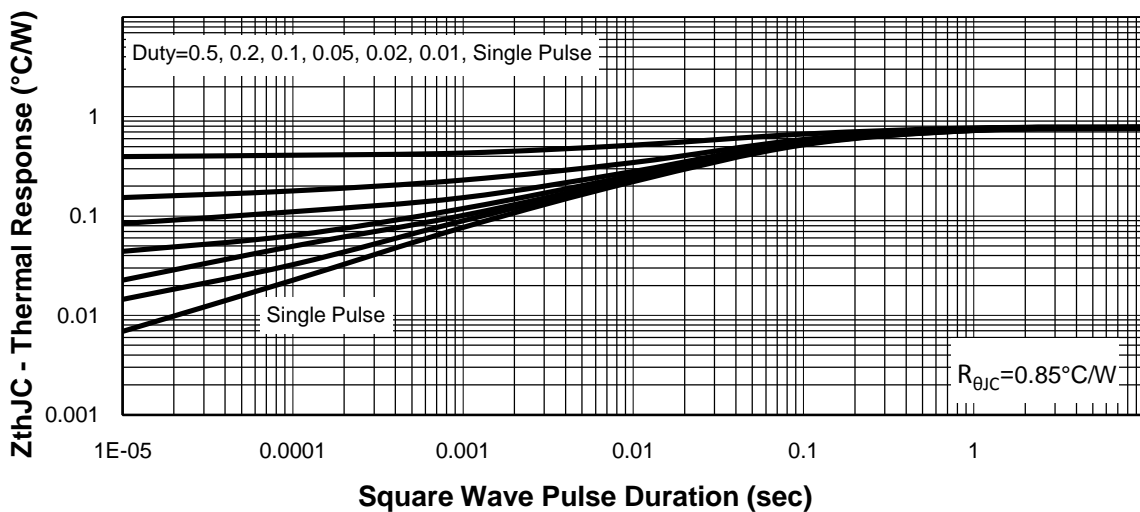
Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU80N15S	RU80N15S	TO263	Tube	50	-	-

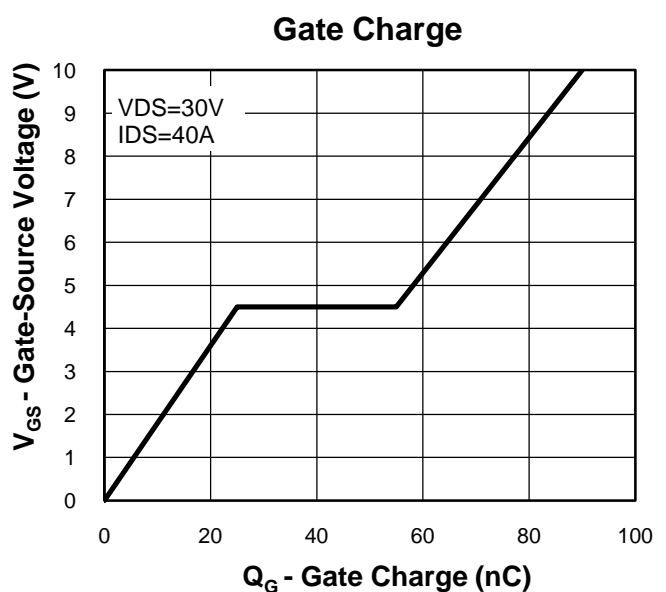
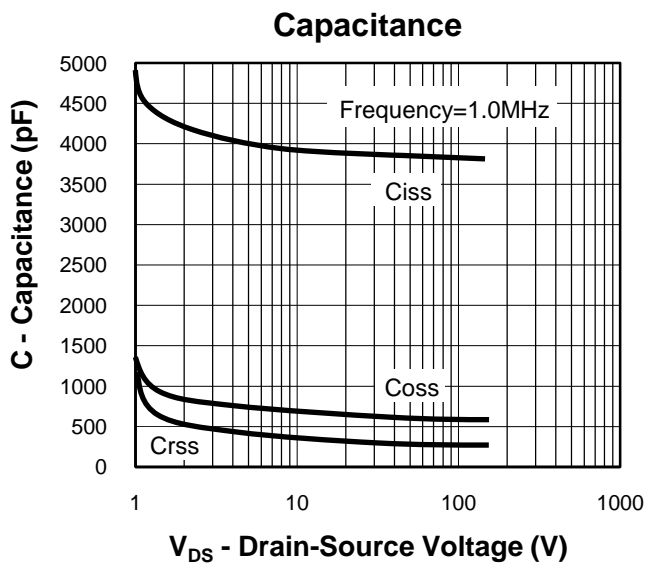
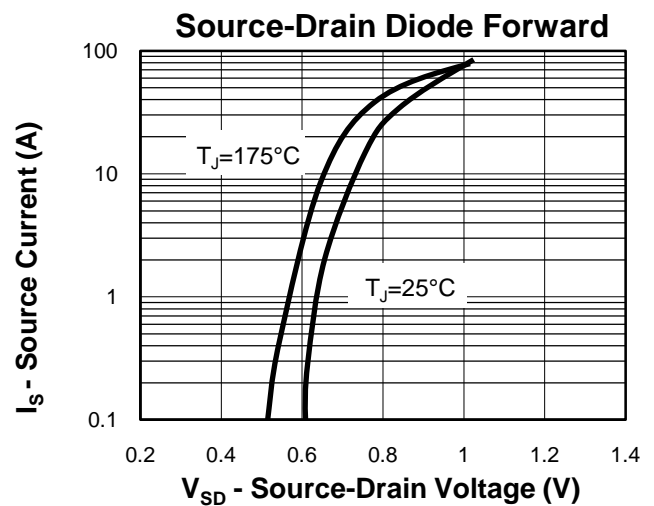
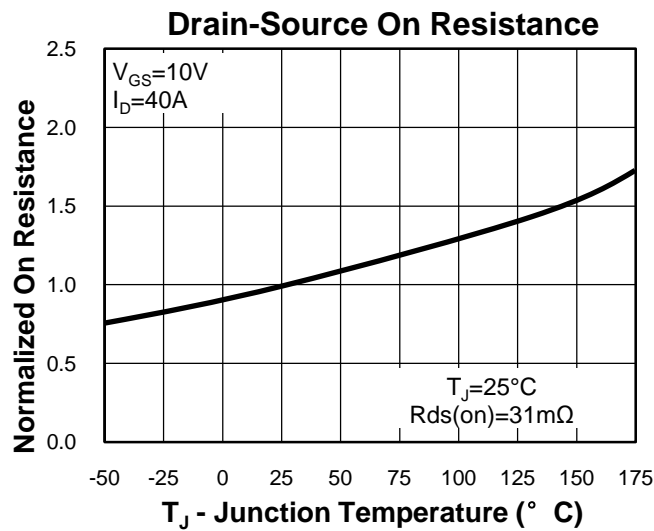
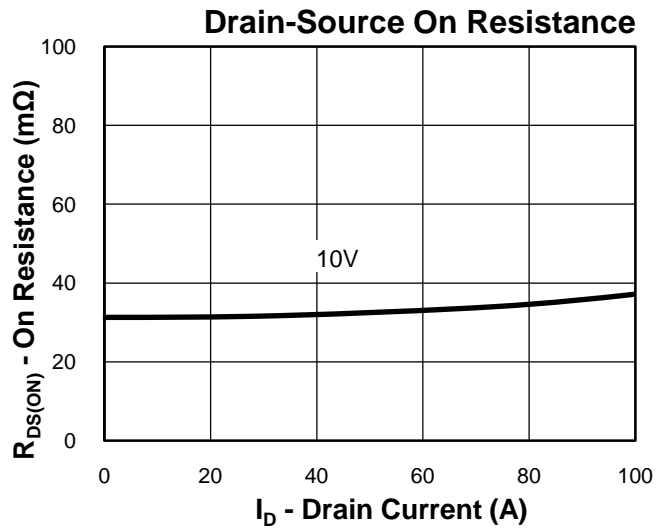
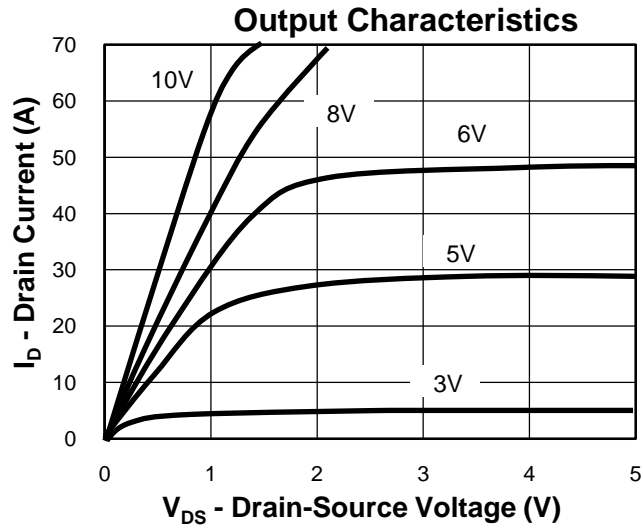
Typical Characteristics



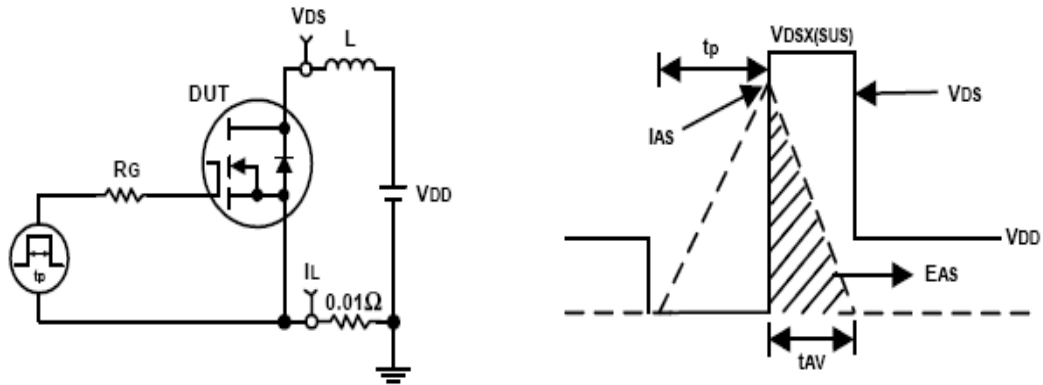
Thermal Transient Impedance



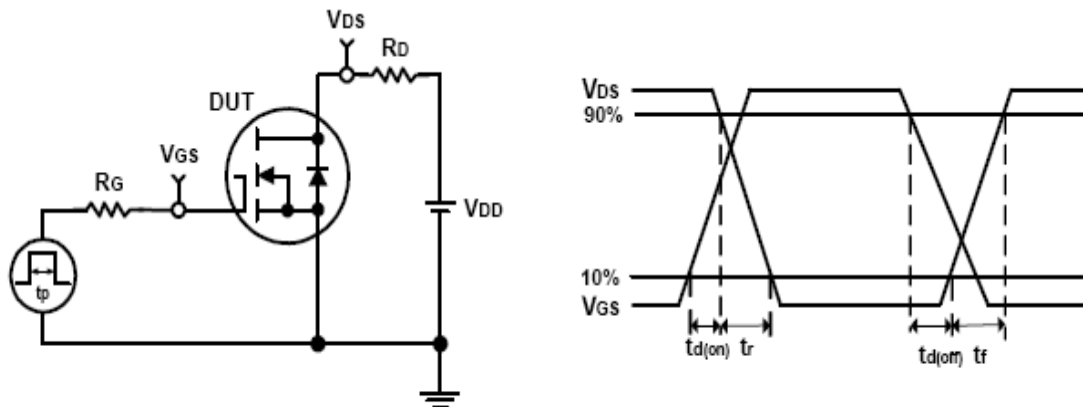
Typical Characteristics



Avalanche Test Circuit and Waveforms

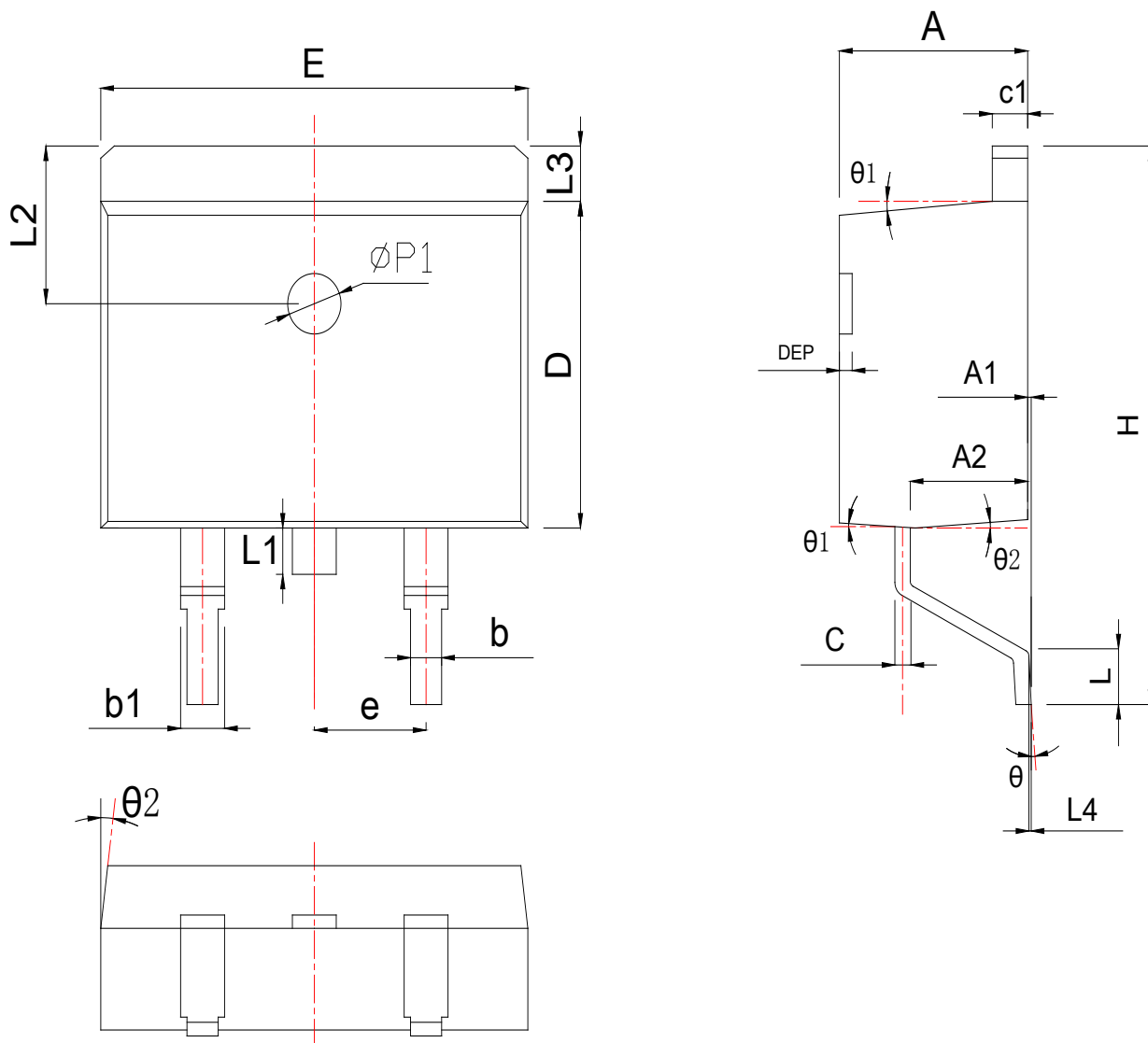


Switching Time Test Circuit and Waveforms



Package Information

TO263



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.55	4.70	0.173	0.179	0.185	L	2.00	2.30	2.60	0.079	0.091	0.102
A1	0.00	0.10	0.25	0.000	0.005	0.010	L3	1.17	1.29	1.40	0.046	0.051	0.055
A2	2.59	2.69	2.79	0.102	0.106	0.110	L1	*	*	1.70	*	*	0.067
b	0.77	*	0.90	0.030		0.035	L4	0.25 BSC			0.01 BSC		
b1	1.23	*	1.36	0.048		0.054	L2	2.50 REF			0.098 REF		
c	0.34	*	0.47	0.013		0.019	θ	0°	*	8°	0°	*	8°
c1	1.22	*	1.32	0.048		0.052	θ1	5°	7°	9°	5°	7°	9°
D	8.60	8.70	8.80	0.339	0.343	0.346	θ2	1°	3°	5°	1°	3°	5°
E	10.00	10.13	10.26	0.394	0.399	0.404	DEP	0.05	0.10	0.20	0.002	0.004	0.008
e	2.54BSC			0.100BSC			Φp1	1.40	1.50	1.60	0.055	0.059	0.063
H	14.70	15.10	15.50	0.579	0.594	0.610							

Customer Service**Worldwide Sales and Service:**

Sales@ruichips.com

Technical Support:

Technical@ruichips.com

Investor Relations Contacts:

Investor@ruichips.com

Marcom Contact:

Marcom@ruichips.com

Editorial Contact:

Editorial@ruichips.comm

HR Contact:

HR@ruichips.com

Legal Contact:

Legal@ruichips.com

Shen Zhen RUICHIPS Semiconductor CO., LTDRoom 501, the 5floor An Tong Industrial Building,
NO.207 Mei Hua Road Fu Tian Area Shen Zhen City, CHINA**TEL:** (86-755) 8311-5334**FAX:** (86-755) 8311-4278**E-mail:** Sales-SZ@ruichips.com